Andreas Othonos

List of Publications by Year
in descending order

155 papers	3,922 citations	159358 30 h-index	149479 56 g-index
157 all docs	157 docs citations	157 times ranked	4447 citing authors

#	Article	IF	Citations
1	Fiber Bragg gratings. Review of Scientific Instruments, 1997, 68, 4309-4341.	0.6	756
2	Probing ultrafast carrier and phonon dynamics in semiconductors. Journal of Applied Physics, 1998, 83, 1789-1830.	1.1	371
3	Fiber Bragg Gratings: Fundamentals and Applications in Telecommunications and Sensing. Physics Today, 2000, 53, 61-62.	0.3	142
4	Ultrafast dynamics of nonlinear absorption in lowâ€temperatureâ€grown GaAs. Applied Physics Letters, 1996, 68, 2544-2546.	1.5	103
5	Distributed strain measurement based on a fiber Bragg grating and its reflection spectrum analysis. Optics Letters, 1996, 21, 1405.	1.7	95
6	Optical Properties of Organic Semiconductor Blends with Nearâ€Infrared Quantumâ€Dot Sensitizers for Light Harvesting Applications. Advanced Energy Materials, 2011, 1, 802-812.	10.2	88
7	Fibre Bragg Gratings. , 2006, , 189-269.		75
8	A multiplexed Bragg grating fiber laser sensor system. IEEE Photonics Technology Letters, 1993, 5, 1112-1114.	1.3	71
9	Superimposed multiple Bragg gratings. Electronics Letters, 1994, 30, 1972-1974.	0.5	71
10	Raman spectroscopy using a fiber optic probe with subwavelength aperture. Applied Physics Letters, 1994, 64, 1768-1770.	1.5	64
11	Influence of temperature and modulation frequency on the thermal activation coupling term in laser photothermal theory. Journal of Applied Physics, 2002, 92, 1280-1285.	1.1	64
12	Long-Lived Hot Carriers in Formamidinium Lead Iodide Nanocrystals. Journal of Physical Chemistry C, 2017, 121, 12434-12440.	1.5	62
13	Bragg Gratings in Optical Fibers: Fundamentals and Applications. , 2000, , 79-187.		53
14	Correlation of hot-phonon and hot-carrier kinetics in Ge on a picosecond time scale. Physical Review B, 1991, 43, 6682-6690.	1.1	47
15	Spectroscopy and analysis of radiative and nonradiative processes inTi3+:Al2O3crystals. Physical Review B, 1993, 48, 5922-5934.	1.1	45
16	Phase shifted Bragg gratings formed in optical fibres by post-fabrication thermal processing. Optics Communications, 1996, 127, 200-204.	1.0	45
17	Absolute nonradiative energy-conversion-efficiency spectra inTi3+:Al2O3crystals measured by noncontact quadrature photopyroelectric spectroscopy. Physical Review B, 1993, 48, 6808-6821.	1.1	41
18	Novel and improved methods of writing Bragg gratings with phase masks. IEEE Photonics Technology Letters, 1995, 7, 1183-1185.	1.3	41

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19	Nonâ€contacting measurements of photocarrier lifetimes in bulkâ€and polycrystalline thinâ€film Si photoconductive devices by photothermal radiometry. Journal of Applied Physics, 1996, 80, 5332-5341.	1.1	40
20	Ultrafast transient photoinduced absorption in silicon nanocrystals: Coupling of oxygen-related states to quantized sublevels. Applied Physics Letters, 2007, 90, 171103.	1.5	40
21	Carrier dynamics and conductivity of SnO2 nanowires investigated by time-resolved terahertz spectroscopy. Applied Physics Letters, 2012, 100, .	1.5	40
22	Characterization of reflectivity inversion, Î±- and Î²-phase transitions and nanostructure formation in hydrogen activated thin Pd films on silicon based substrates. Journal of Applied Physics, 2002, 91, 3829-3840.	1.1	39
23	Ultrafast hole carrier relaxation dynamics in p-type CuO nanowires. Nanoscale Research Letters, 2011, 6, 622.	3.1	39
24	Single-Exciton Gain and Stimulated Emission Across the Infrared Telecom Band from Robust Heavily Doped PbS Colloidal Quantum Dots. Nano Letters, 2020, 20, 5909-5915.	4.5	38
25	Ultralongâ€Range Polaritonâ€Assisted Energy Transfer in Organic Microcavities. Angewandte Chemie - International Edition, 2021, 60, 16661-16667.	7.2	37
26	Tin Oxide Nanowires: The Influence of Trap States on Ultrafast Carrier Relaxation. Nanoscale Research Letters, 2009, 4, 828-833.	3.1	35
27	Optical properties of conjugated poly(3-hexylthiophene)/[6,6]-phenylC61-butyric acid methyl ester composites. Journal of Applied Physics, 2007, 102, 083104.	1.1	34
28	The Influence of Doping on the Optoelectronic Properties of PbS Colloidal Quantum Dot Solids. Scientific Reports, 2016, 6, 18735.	1.6	33
29	Raman spectroscopy and spreading resistance analysis of phosphorus implanted and annealed silicon. Journal of Applied Physics, 1994, 75, 8032-8038.	1.1	32
30	Ultrafast carrier dynamics in band edge and broad deep defect emission ZnSe nanowires. Applied Physics Letters, 2007, 91, .	1.5	30
31	Ultrafast Carrier Relaxation in InN Nanowires Grown by Reactive Vapor Transport. Nanoscale Research Letters, 2009, 4, .	3.1	30
32	Structure, morphology, and photoluminescence of porous Si nanowires: effect of different chemical treatments. Nanoscale Research Letters, 2013, 8, 383.	3.1	30
33	Efficient Optical Amplification in the Nanosecond Regime from Formamidinium Lead Iodide Nanocrystals. ACS Photonics, 2018, 5, 907-917.	3.2	30
34	The role of surface vibrations and quantum confinement effect to the optical properties of very thin nanocrystalline silicon films. Journal of Applied Physics, 2007, 102, 083534.	1.1	29
35	Ultrafast time-resolved spectroscopy of In2O3 nanowires. Journal of Applied Physics, 2009, 106, 084307.	1.1	29
36	Sizeâ€Dependent Charge Transfer in Blends of PbS Quantum Dots with a Lowâ€Gap Siliconâ€Bridged Copolymer. Advanced Energy Materials, 2013, 3, 1490-1499.	10.2	29

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37	Large ultrafast optical nonlinearities in As-rich GaAs. Electronics Letters, 1994, 30, 1704-1706.	0.5	28
38	Photothermal radiometric investigation of implanted silicon: The influence of dose and thermal annealing. Applied Physics Letters, 1996, 69, 821-823.	1.5	28
39	Ultrafast carrier dynamics on conjugated poly(3-hexylthiophene)/[6,6]-phenylC61-butyric acid methyl ester composites. Applied Physics Letters, 2007, 91, 111117.	1.5	28
40	Ellipsometric analysis of ion-implanted polycrystalline silicon films before and after annealing. Thin Solid Films, 2006, 496, 253-258.	0.8	26
41	Ultrafast Dynamics of Localized and Delocalized Polaron Transitions in P3HT/PCBM Blend Materials: The Effects of PCBM Concentration. Nanoscale Research Letters, 2009, 4, 1475-1480.	3.1	26
42	Quantum confinement and interface structure of Si nanocrystals of sizes 3â€“5nm embedded in a-SiO2. Physica E: Low-Dimensional Systems and Nanostructures, 2007, 38, 128-134.	1.3	24
43	An investigation into the conversion of In2O3 into InN nanowires. Nanoscale Research Letters, 2011, 6, 311.	3.1	24
44	Carrier dynamics in Î²-Ga2O3 nanowires. Journal of Applied Physics, 2010, 108, 124302.	1.1	23
45	Fiber Bragg grating laser sensor. Optical Engineering, 1993, 32, 2841.	0.5	22
46	Surface-Related States in Oxidized Silicon Nanocrystals Enhance Carrier Relaxation and Inhibit Auger Recombination. Nanoscale Research Letters, 2008, 3, .	3.1	22
47	Ultrafast transient spectroscopy and photoluminescence properties of V2O5 nanowires. Applied Physics Letters, 2013, 103, .	1.5	21
48	Ultrafast time-resolved spectroscopy of ZnSe nanowires: Carrier dynamics of defect-related states. Journal of Alloys and Compounds, 2009, 483, 600-603.	2.8	20
49	Influence of grain size on ultrafast carrier dynamics in thin nanocrystalline silicon films. Applied Physics Letters, 2007, 90, 191114.	1.5	19
50	Optically thin palladium films on silicon-based substrates and nanostructure formation: effects of hydrogen. Applied Surface Science, 2000, 161, 54-60.	3.1	18
51	Instrumentation for the monitoring of toxic pollutants in water resources by means of neural network analysis of absorption and fluorescence spectra. Sensors and Actuators B: Chemical, 2007, 121, 231-237.	4.0	18
52	Broad compositional tunability of indium tin oxide nanowires grown by the vapor-liquid-solid mechanism. APL Materials, 2014, 2, .	2.2	18
53	Study of the annealing kinetic effect and implantation energy on phosphorus-implanted silicon wafers using spectroscopic ellipsometry. Journal of Applied Physics, 2006, 99, 123514.	1.1	17
54	Sn doped Î²-Ga2O3 and Î²-Ga2S3 nanowires with red emission for solar energy spectral shifting. Journal of Applied Physics, 2015, 118, .	1.1	17

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55	Defect states of chemical vapor deposition grown GaN nanowires: Effects and mechanisms in the relaxation of carriers. Journal of Applied Physics, 2009, 106, 054311.	1.1	16
56	A systematic investigation into the conversion of Î²-Ga2O3 to GaN nanowires using NH3 and H2: Effects on the photoluminescence properties. Journal of Applied Physics, 2010, 108, 124319.	1.1	15
57	Photophysics of PbS Quantum Dot Films Capped with Arsenic Sulfide Ligands. Advanced Energy Materials, 2014, 4, 1301547.	10.2	15
58	Ultrafast Spectroscopy and Red Emission from Î²-Ga2O3/Î²-Ga2S3 Nanowires. Nanoscale Research Letters, 2015, 10, 1016.	3.1	15
59	Unraveling the Radiative Pathways of Hot Carriers upon Intense Photoexcitation of Lead Halide Perovskite Nanocrystals. ACS Nano, 2019, 13, 5799-5809.	7.3	15
60	Lowâ€Threshold, Highly Stable Colloidal Quantum Dot Shortâ€Wave Infrared Laser enabled by Suppression of Trapâ€Assisted Auger Recombination. Advanced Materials, 2022, 34, e2107532.	11.1	15
61	Single-ended infrared photothermal radiometric measurement of quantum efficiency and metastable lifetime in solid-state laser materials: The case of ruby (Cr/sup 3+/:Al/sub 2/O/sub 3/). IEEE Journal of Quantum Electronics, 1993, 29, 1498-1504.	1.0	14
62	Femtosecond Dynamics in Single Wall Carbon Nanotube/Poly(3-Hexylthiophene) Composites. Nanoscale Research Letters, 2008, 3, .	3.1	14
63	Synthesis of Tin Nitride Sn x N y Nanowires by Chemical Vapour Deposition. Nanoscale Research Letters, 2009, 4, 1103-1109.	3.1	14
64	High yieldâ€“low temperature growth of indium sulphide nanowires via chemical vapor deposition. Journal of Crystal Growth, 2010, 312, 656-661.	0.7	14
65	Gallium hydride vapor phase epitaxy of GaN nanowires. Nanoscale Research Letters, 2011, 6, 262.	3.1	14
66	Photovoltaic limitations of BODIPY:fullerene based bulk heterojunction solar cells. Synthetic Metals, 2017, 226, 25-30.	2.1	14
67	Surface Functionalization of CsPbBr₃ Îanocrystals for Photonic Applications. ACS Applied Nano Materials, 2021, 4, 5084-5097.	2.4	14
68	Spectrally broadband Bragg grating mirror for an erbiumâ€doped fiber laser. Optical Engineering, 1996, 35, 1088.	0.5	13
69	Ultrafast pulsed laser deposition of carbon nanostructures: Structural and optical characterization. Applied Surface Science, 2013, 278, 101-105.	3.1	13
70	Observation of the Direct Energy Band Gaps of Defect-Tolerant Cu3N by Ultrafast Pump-Probe Spectroscopy. Journal of Physical Chemistry C, 2020, 124, 3459-3469.	1.5	13
71	Low Temperature Growth of In2O3and InN Nanocrystals on Si(111) via Chemical Vapour Deposition Based on the Sublimation of NH4Cl in In. Nanoscale Research Letters, 2009, 4, 491-7.	3.1	12
72	Fluorescence studies of multiple-photon ionization processes: Four- and five-photon ionization of Sr at wavelengths of 558â€“590 nm. Physical Review A, 1989, 39, 3392-3400.	1.0	11

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73	Zn3N2 nanowires: growth, properties and oxidation. Nanoscale Research Letters, 2013, 8, 221.	3.1	11
74	Impact of Oxygen on the Properties of Cu₃N and Cu_{3â€“x}N_{1â€“x}O_x. Journal of Physical Chemistry C, 2021, 125, 3680-3688.	1.5	11
75	Narrow linewidth excimer laser for inscribing Bragg gratings in optical fibers. Review of Scientific Instruments, 1995, 66, 3112-3115.	0.6	10
76	Determining erbium distribution in optical fibers using phase-sensitive confocal microscopy. Optical Engineering, 1995, 34, 3451.	0.5	10
77	Effects of Ge concentration, boron co-doping, and hydrogenation on fiber Bragg grating characteristics. Microwave and Optical Technology Letters, 2005, 44, 148-152.	0.9	10
78	Ultrafast carrier dynamics in InxGa1âˆ’xN (0001) epilayers: Effects of high fluence excitation. Applied Physics Letters, 2006, 88, 121128.	1.5	10
79	Femtosecond Carrier Dynamics in In2O3Nanocrystals. Nanoscale Research Letters, 2009, 4, 526-531.	3.1	10
80	A systematic study of the nitridation of SnO2 nanowires grown by the vapor liquid solid mechanism. Journal of Crystal Growth, 2012, 340, 28-33.	0.7	10
81	Current Transport Properties of CuS/Sn:In₂O₃ versus CuS/SnO₂ Nanowires and Negative Differential Resistance in Quantum Dot Sensitized Solar Cells. Journal of Physical Chemistry C, 2016, 120, 11-20.	1.5	10
82	Hydrogen gas detection via photothermal deflection measurement. Review of Scientific Instruments, 1997, 68, 3544-3552.	0.6	9
83	Ultrafast dynamics in phosphorus-implanted silicon wafers:â€ƒThe effects of annealing. Physical Review B, 2002, 66, .	1.1	9
84	Structural properties of SnO₂ nanowires and the effect of donor like defects on its charge distribution. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 226-229.	0.8	9
85	Surface passivation and conversion of SnO2 to SnS2 nanowires. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2015, 198, 10-13.	1.7	8
86	Epitaxial highly ordered Sb:SnO2 nanowires grown by the vapor liquid solid mechanism on m-, r- and a-Al2O3. Nanoscale Advances, 2019, 1, 1980-1990.	2.2	8
87	Ultralongâ€Range Polaritonâ€Assisted Energy Transfer in Organic Microcavities. Angewandte Chemie, 2021, 133, 16797-16803.	1.6	8
88	Controlling the optical properties of nanostructured oxide-based polymer films. Scientific Reports, 2021, 11, 16009.	1.6	8
89	p-Type Iodine-Doping of Cu3N and Its Conversion to Î³-CuI for the Fabrication of Î³-CuI/Cu3N p-n Heterojunctions. Electronic Materials, 2022, 3, 15-26.	0.9	8
90	Free carrier and lattice-heating-induced changes to the reflectivity of epitaxial GeSi alloys following picosecond pulse excitation. Solid State Communications, 1992, 82, 325-328.	0.9	7

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91	Optical spectroscopy on implanted and annealed silicon wafers: Plasma resonance wavelength. Journal of Applied Physics, 1994, 75, 3377-3384.	1.1	7
92	Temperature-induced reflectivity changes and activation of hydrogen sensitive optically thin palladium films on silicon oxide. Review of Scientific Instruments, 1998, 69, 3331-3338.	0.6	7
93	Bragg gratings in optical fibers. , 2001, , 367-480.		7
94	Optical Characterization of Varnish Films by Spectroscopic Ellipsometry for Application in Artwork Conservation. Applied Spectroscopy, 2005, 59, 94-99.	1.2	7
95	Probing carrier dynamics in implanted and annealed polycrystalline silicon thin films using white light. Applied Physics Letters, 2006, 88, 181107.	1.5	7
96	Femtosecond carrier dynamics of InxGa1â^'xN thin films grown on GaN (0001): Effect of carrier-defect scattering. Journal of Applied Physics, 2007, 102, 073104.	1.1	7
97	Timeâ€resolved ultrafast carrier dynamics in asâ€grown nanocrystalline silicon films: the effect of film thickness and grain boundaries. Physica Status Solidi - Rapid Research Letters, 2008, 2, 19-21.	1.2	7
98	Carrier relaxation dynamics in SnxNy nanowires grown by chemical vapor deposition. Journal of Applied Physics, 2009, 106, 114303.	1.1	7
99	Influence of surface-related states on the carrier dynamics in (Ga,In)N/GaN single quantum wells. Applied Physics Letters, 2009, 94, .	1.5	7
100	Hydride-assisted growth of GaN nanowires on Au/Si(001) via the reaction of Ga with NH3 and H2. Journal of Crystal Growth, 2010, 312, 2631-2636.	0.7	7
101	Electrical, structural, and optical properties of sulfurized Sn-doped In2O3 nanowires. Nanoscale Research Letters, 2015, 10, 995.	3.1	7
102	Coreâ€“shell PbS/Sn:In₂O₃ and branched PbIn₂S₄/Sn:In₂O₃ nanowires in quantum dot sensitized solar cells. Nanotechnology, 2017, 28, 054004.	1.3	7
103	The influence of additives in the stoichiometry of hybrid lead halide perovskites. AIP Advances, 2017, 7, .	0.6	7
104	Flexible, Free-Standing Polymer Membranes Sensitized by CsPbX3 Nanocrystals as Gain Media for Low Threshold, Multicolor Light Amplification. ACS Photonics, 2022, 9, 2385-2397.	3.2	7
105	Hot-carrier dynamics in Ge on single picosecond timescales: Comparing Raman and reflectivity experiments with a self-consistent kinetic model. Solid-State Electronics, 1989, 32, 1573-1577.	0.8	6
106	Determination of erbium distribution in optical fibers using confocal optical microscopy. IEEE Photonics Technology Letters, 1994, 6, 437-439.	1.3	6
107	Photoluminescence measurements on phosphorus implanted silicon: Annealing kinetics of defects. Journal of Applied Physics, 1995, 78, 796-800.	1.1	6
108	Photothermal radiometric and spectroscopic measurements on silicon nitride thin films. Journal of Applied Physics, 1997, 82, 6215-6219.	1.1	6

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109	Direct observation of excitons in polymer/carbon nanotube composites at room temperature: The influence of nanotube concentration. Diamond and Related Materials, 2008, 17, 1600-1603.	1.8	6
110	Monitoring Charge Exchange in P3HT-Nanotube Composites Using Optical and Electrical Characterisation. Nanoscale Research Letters, 2009, 4, 635-639.	3.1	6
111	SnO2/PbOx (x = 1, 2) Coreâ€“Shell Nanowires and Their Growth on C-Fiber Networks for Energy Storage. Journal of Physical Chemistry C, 2018, 122, 25813-25821.	1.5	6
112	Doping and Conductivity Limitations in Sb:SnO₂ Nanowires Grown by the Vapor Liquid Solid Mechanism. Journal of Physical Chemistry C, 2018, 122, 22709-22716.	1.5	6
113	Multi-wavelength Raman probing of phosphorus implanted silicon wafers. Nuclear Instruments & Methods in Physics Research B, 1996, 117, 367-374.	0.6	5
114	Spatial dependence of ultrafast carrier recombination centers of phosphorus-implanted and annealed silicon wafers. Applied Physics Letters, 2002, 81, 856-858.	1.5	5
115	Photomodulated thermoreflectance detection of hydrogen at elevated temperatures: a detection limit. Applied Physics Letters, 2003, 82, 904-906.	1.5	5
116	Temporal evolution of effects of ultrafast carrier dynamics in In0.33Ga0.67N: above and near the bandgap. Semiconductor Science and Technology, 2007, 22, 158-162.	1.0	5
117	Enhanced growth and photoluminescence properties of SnxNy (x>y) nanowires grown by halide chemical vapor deposition. Journal of Crystal Growth, 2011, 316, 25-29.	0.7	5
118	FÃ¶rster resonant energy transfer from an inorganic quantum well to a molecular material: Unexplored aspects, losses, and implications to applications. Journal of Chemical Physics, 2015, 143, 214701.	1.2	5
119	Sn:In₂O₃ and Sn:In₂O₃/NiS₂ Coreâ€“Shell Nanowires on Ni, Mo Foils and C Fibers for H₂ and O₂ Generation. Journal of Physical Chemistry C, 2017, 121, 27839-27848.	1.5	5
120	Excitonâ€“Ligand Interactions in PbS Quantum Dots Capped with Metal Chalcogenides. Journal of Physical Chemistry C, 2020, 124, 27848-27857.	1.5	5
121	Diagnostics of nonradiative defects in the bulk and surface of Brewster-cut Ti:sapphire laser materials using photothermal radiometry. IEEE Journal of Quantum Electronics, 1997, 33, 2301-2310.	1.0	4
122	Optical and structural properties of implanted Si wafers: the effects of implantation energy and subsequent isochronal annealing temperature. Semiconductor Science and Technology, 2006, 21, 1059-1063.	1.0	4
123	Ultrafast time-resolved spectroscopy of Si nanocrystals embedded in SiO2 matrix. Journal of Alloys and Compounds, 2009, 483, 597-599.	2.8	4
124	Excitation dynamics of a low bandgap silicon-bridged dithiophene copolymer and its composites with fullerenes. Applied Physics Letters, 2012, 100, 153303.	1.5	4
125	The nitridation of ZnO nanowires. Nanoscale Research Letters, 2012, 7, 175.	3.1	4
126	Concentration and excitation effects on the exciton dynamics of poly(3-hexylthiophene)/PbS quantum dot blend films. Nanotechnology, 2013, 24, 235707.	1.3	4

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127	Ultraviolet emission from low resistance Cu2SnS3/SnO2 and CuInS2/Sn:In2O3 nanowires. APL Materials, 2014, 2, 116107.	2.2	4
128	Fine art painting characterization by spectroscopic ellipsometry: preliminary measurements on varnish layers. Thin Solid Films, 2004, 455-456, 207-212.	0.8	3
129	Femtosecond carrier dynamics in implanted and highly annealed polycrystalline silicon. Semiconductor Science and Technology, 2006, 21, 1041-1046.	1.0	3
130	Transient Photoinduced Absorption in Ultrathin As-grown Nanocrystalline Silicon Films. Nanoscale Research Letters, 2008, 3, .	3.1	3
131	Pb doping of In2O3 and their conversion to highly conductive PbS/In2S3â^'3xO3x nanowires with infra red emission. Materials Letters, 2016, 166, 129-132.	1.3	3
132	High-Temperature Pb Doping of SnO₂ and Growth Limitations of Pb_xSn_{1â€“x}O₂ Nanowires Versus Low-Temperature Growth of Pb_xSn_{1â€“x}O for Energy Storage and Conversion. Journal of Physical Chemistry C, 2019, 123, 16415-16423.	1.5	3
133	Optical Transitions in Silver Indium Selenide Nanocrystals: Implications for Light-Emitting and Light-Imaging Applications. ACS Applied Nano Materials, 2021, 4, 11239-11248.	2.4	3
134	Picosecond Raman Scattering From Non-Equilibrium Collective Modes In Diamond And Zincblende Semiconductors. , 1988, , .		2
135	Reconstruction Mechanisms in Ion Implanted and Annealed Silicon Wafers. Defect and Diffusion Forum, 1995, 117-118, 45-64.	0.4	2
136	Determination of critical points on silicon nanofilms: surface and quantum confinement effects. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3776-3779.	0.8	2
137	Optical properties of polyelectrolyte quantum dot multilayer films prepared using the layer by layer self-assembly method. Journal of Applied Physics, 2008, 103, 083511.	1.1	2
138	Carrier dynamics in InS nanowires grown via chemical vapor deposition. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 2258-2262.	0.8	2
139	(Invited) Optical Response of II-VI ZnSe Nanowires. ECS Transactions, 2010, 28, 193-202.	0.3	2
140	Well-defined fluoro- and carbazole-containing diblock copolymers: synthesis, characterization and immobilization onto Au-coated silicon surfaces. RSC Advances, 2012, 2, 8741.	1.7	2
141	Sulfur doping of M/In2O3 (M=Al,W) nanowires with room temperature near infra red emission. AIP Advances, 2015, 5, 097101.	0.6	2
142	<title>Fiber laser sensor array</title>. , 1993, , .		1
143	High-Resolution Quadrature Photopyroelectric Spectroscopy of a-Si:H Thin Films Deposited on Silicon Wafers. Applied Spectroscopy, 1995, 49, 819-824.	1.2	1
144	Photomodulated thermoreflectance investigation at elevated temperatures: plasma versus thermal effect. Applied Physics Letters, 2003, 82, 1132-1134.	1.5	1

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145	High-temperature photomodulated thermoreflectance measurements on phosphorus implanted and annealed silicon wafers. Journal of Applied Physics, 2003, 94, 7121-7127.	1.1	1
146	Femtosecond time-resolved study in InxGa1â^'xN (0001) ultrathin epilayers: Effects of high indium mole fraction and thickness of the films. Applied Physics Letters, 2006, 89, 241109.	1.5	1
147	Observation of Quantum Confinement Effects with cmd="newline" Ultrashort Excitation in the Vicinity of Direct Critical Points cmd="newline" in Silicon Nanofilms. Research Letters in Physics, 2008, 2008, 1-5.	0.2	1
148	Synthesis of hybrid polymethacrylateâ€“noble metal (M = Au, Pd) nanoparticles for the growth of metal-oxide semiconductor nanowires. RSC Advances, 2012, 2, 4370.	1.7	1
149	Ultrafast dynamics and short-lived carriers in Cu nitride and oxynitride layers. Journal of Applied Physics, 2020, 128, 125704.	1.1	1
150	Chapter 3 Photoluminescence and Raman Scattering of Ion Implanted Semiconductors. Influence of Annealing. Semiconductors and Semimetals, 1997, 46, 73-114.	0.4	0
151	Thermal wave hydrogen gas sensor characterized via photothermal deflection measurements. , 1999, , .		0
152	Photothermal radiometric measurements on metal contaminated silicon wafers. , 1999, , .		0
153	Room temperature hydrogen gas detection with optically thin palladium films on silicon oxide using photomodulated thermoreflectance. , 1999, , .		0
154	Ultrafast carrier dynamics in highly implanted and annealed polycrystalline silicon films. Journal of Physics: Conference Series, 2005, 10, 263-266.	0.3	0
155	Femtosecond laser inscription of Bragg and complex gratings in coated and encapsulated silica and low-loss polymer optical fibers. , 2015, , .		0